50 V; 3 A NPN low VCEsat transistor 1 January 2023

Product data sheet

1. General description

NPN low V_{CEsat} transistor in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package.

PNP complement: PBSS5350T

2. Features and benefits

- Low collector-emitter saturation voltage V_{CEsat} and corresponding low R_{CEsat}
- High collector current capability
- · High collector current gain
- · Improved efficiency due to reduced heat generation

3. Applications

- Power management applications
- · Low and medium power DC/DC converters
- Supply line switching
- Battery chargers
- Linear voltage regulation with low voltage drop-out (LDO)

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	50	V
I _C	collector current		-	-	2	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms	-	-	5	Α
R _{CEsat}	collector-emitter saturation resistance	I_C = 2 A; I_B = 200 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	100	130	mΩ



50 V; 3 A NPN low VCEsat transistor

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	3	C
2	Е	emitter		j
3	С	collector		В — (
			SOT23	 E sym123

6. Ordering information

Table 3. Ordering information

Type number Package							
	Name	Description	Version				
PBSS4350T	SOT23	plastic, surface-mounted package; 3 terminals; 1.9 mm pitch; 2.9 mm x 1.3 mm x 1 mm body	SOT23				

7. Marking

Table 4. Marking codes

Type number	Marking code[1]
PBSS4350T	ZC%

[1] % = placeholder for manufacturing site code

50 V; 3 A NPN low VCEsat transistor

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter		-	50	V
V _{CEO}	collector-emitter voltage	open base		-	50	V
V _{EBO}	emitter-base voltage	open collector		-	5	V
I _C	collector current			-	2	Α
I _{CRM}	repetitive peak collector current	$\delta \le 0.25; t_p \le 100 \text{ ms}$		-	3	А
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	5	Α
I _B	base current			-	0.5	Α
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	300	mW
			[2]	-	480	mW
			[3]	-	540	mW
			[1] [4]	-	1.2	W
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-65	150	°C
T _{stg}	storage temperature			-65	150	°C

- Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm². Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².
- Operated under pulsed conditions: $t_p \le 100 \text{ ms}$; $\delta \le 0.25$.

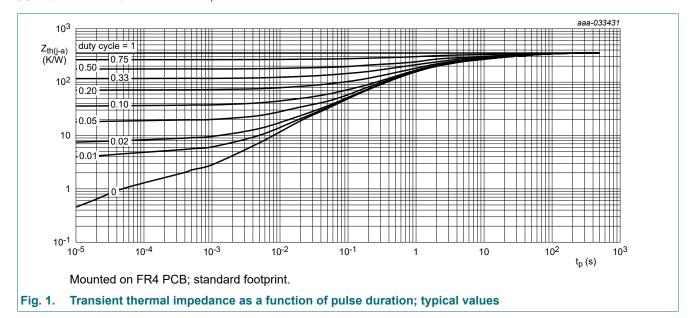
50 V; 3 A NPN low VCEsat transistor

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
ui(j-a)	thermal resistance from junction to ambient	[:	[1]	-	-	417	K/W
			[2]	-	-	260	K/W
			[3]	-	-	230	K/W
			[1] [4]	-	-	104	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm²
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².
- [4] Operated under pulsed conditions: $t_p \le 100$ ms; $\delta \le 0.25$.



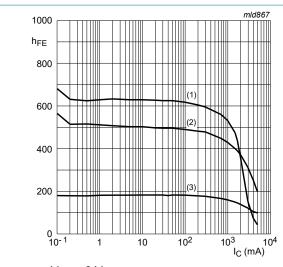
50 V; 3 A NPN low VCEsat transistor

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{(BR)CBO}	collector-base breakdown voltage	$I_C = 100 \ \mu A; I_E = 0 \ A; T_{amb} = 25 \ ^{\circ}C$	50	-	-	V
V _{(BR)CEO}	collector-emitter breakdown voltage	I_C = 10 mA; I_B = 0 A; pulsed; t_p ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	50	-	-	V
V _{(BR)EBO}	emitter-base breakdown voltage (collector open)	$I_E = 100 \mu A; I_C = 0 A; T_{amb} = 25 °C$	5	-	-	V
СВО	collector-base cut-off	V _{CB} = 50 V; I _E = 0 A; T _{amb} = 25 °C	-	-	100	nA
	current	$V_{CB} = 50 \text{ V}; I_E = 0 \text{ A}; T_j = 150 ^{\circ}\text{C}$	-	-	50	μΑ
ЕВО	emitter-base cut-off current	V _{EB} = 5 V; I _C = 0 A; T _{amb} = 25 °C	-	-	100	nA
1 _{FE}	DC current gain	V_{CE} = 2 V; I_{C} = 100 mA; pulsed; $t_{p} \le$ 300 μs; $\delta \le$ 0.02; T_{amb} = 25 °C	300	-	-	
		V_{CE} = 2 V; I_{C} = 500 mA; pulsed; $t_{p} \le$ 300 μs; $\delta \le$ 0.02; T_{amb} = 25 °C	300	-	-	
		V_{CE} = 2 V; I_{C} = 1 A; pulsed; $t_{p} \le 300 \ \mu s$; δ ≤ 0.02; T_{amb} = 25 °C	300	-	-	
		V_{CE} = 2 V; I_{C} = 2 A; pulsed; $t_{p} \le 300 \mu s$; δ ≤ 0.02; T_{amb} = 25 °C	200	-	-	
		V_{CE} = 2 V; I_{C} = 3 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	100	-	-	
V _{CEsat}	collector-emitter	I _C = 500 mA; I _B = 50 mA; T _{amb} = 25 °C	-	-	80	mV
	saturation voltage	I _C = 1 A; I _B = 50 mA; T _{amb} = 25 °C	-	-	160	mV
		I_C = 2 A; I_B = 100 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-	280	mV
		I_C = 2 A; I_B = 200 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-	260	mV
		I_C = 3 A; I_B = 300 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-	370	mV
R _{CEsat}	collector-emitter saturation resistance	I_C = 2 A; I_B = 200 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	100	130	mΩ
√ _{BEsat}	base-emitter saturation voltage	I_C = 2 A; I_B = 100 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-	1.1	V
		I_C = 3 A; I_B = 300 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-	1.2	V
V_{BEon}	base-emitter turn-on voltage	V_{CE} = 2 V; I_{C} = 1 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-	1.2	V
T	transition frequency	V_{CE} = 5 V; I_{C} = 100 mA; f = 100 MHz; T_{amb} = 25 °C	100	-	-	MHz
C _c	collector capacitance	V_{CB} = 10 V; I_{E} = 0 A; i_{e} = 0 A; f = 1 MHz; T_{amb} = 25 °C	-	-	25	pF

50 V; 3 A NPN low VCEsat transistor

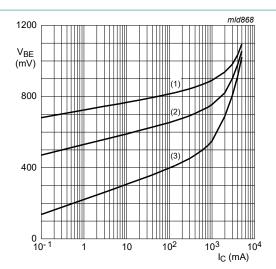


$$V_{CF} = 2 V$$

$$(1) T_{amb} = 150 °C$$

(3)
$$T_{amb} = -55 \, ^{\circ}C$$

Fig. 2. DC current gain as a function of collector current; typical values



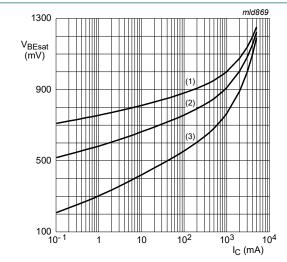
$$V_{CF} = 2 V$$

$$V_{CE} = 2 V$$
(1) $T_{amb} = -55 \,^{\circ}C$
(2) $T_{amb} = 25 \,^{\circ}C$
(3) $T_{amb} = 150 \,^{\circ}C$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 150 \, ^{\circ}C$$

Fig. 3. Base-emitter voltage as a function of collector current; typical values



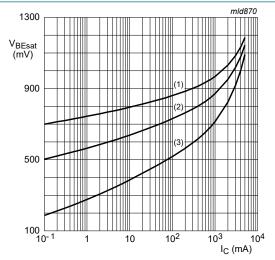
$$I_C/I_B = 10$$

$$(1) T_{amb} = -55 °C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

$$(3) T_{amb} = 150 °C$$

Base-emitter saturation voltage as a function of Fig. 5. Fig. 4. collector current; typical values



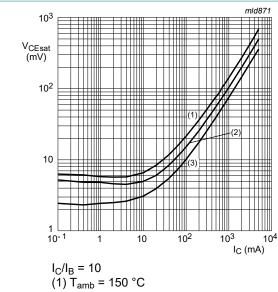
$$I_{\rm C}/I_{\rm B}=20$$

$$(1) T_{amb} = -55 °C$$

(3)
$$T_{amb} = 150 \, ^{\circ}C$$

Base-emitter saturation voltage as a function of collector current; typical values

50 V; 3 A NPN low VCEsat transistor

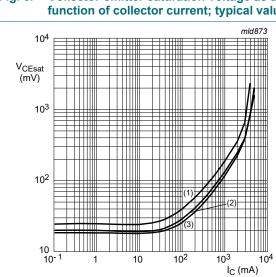


$$(1) T_{amb} = 150 °$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(2) $T_{amb} = 25 \,^{\circ}C$ (3) $T_{amb} = -55 \,^{\circ}C$

Fig. 6. Collector-emitter saturation voltage as a function of collector current; typical values



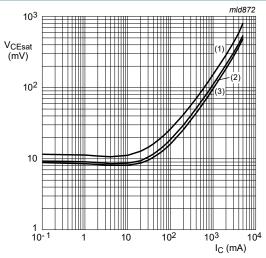
 $I_{\rm C}/I_{\rm B}=50$

(1)
$$T_{amb} = 150 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3) $T_{amb} = -55 \, ^{\circ}C$

Fig. 8. Collector-emitter saturation voltage as a function of collector current; typical values



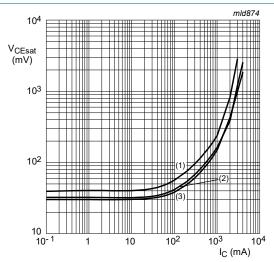
$$I_C/I_B = 20$$

(1) $T_{amb} = 150 \, ^{\circ}C$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(2) $T_{amb} = 25 \,^{\circ}\text{C}$ (3) $T_{amb} = -55 \,^{\circ}\text{C}$

Fig. 7. Collector-emitter saturation voltage as a function of collector current; typical values



 $I_{\rm C}/I_{\rm B} = 100$

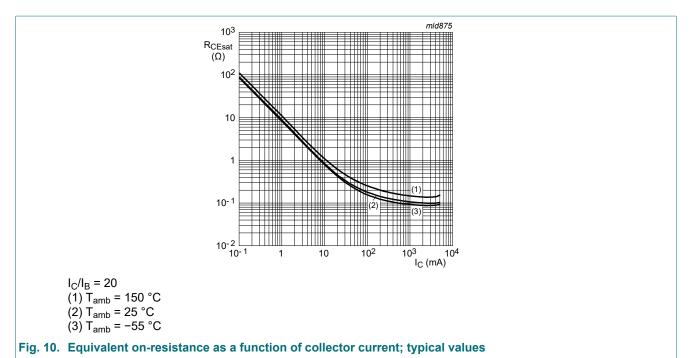
(1)
$$T_{amb} = 150 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3) $T_{amb} = -55$ °C

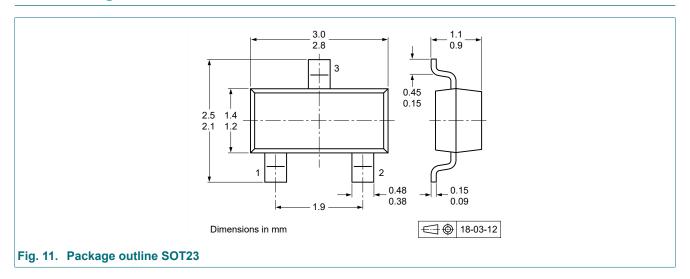
Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values

50 V; 3 A NPN low VCEsat transistor

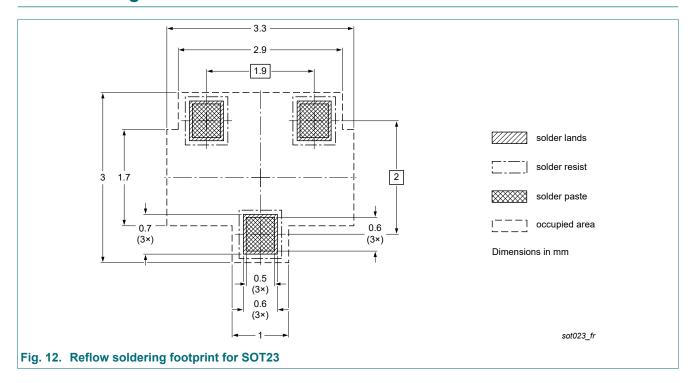


50 V; 3 A NPN low VCEsat transistor

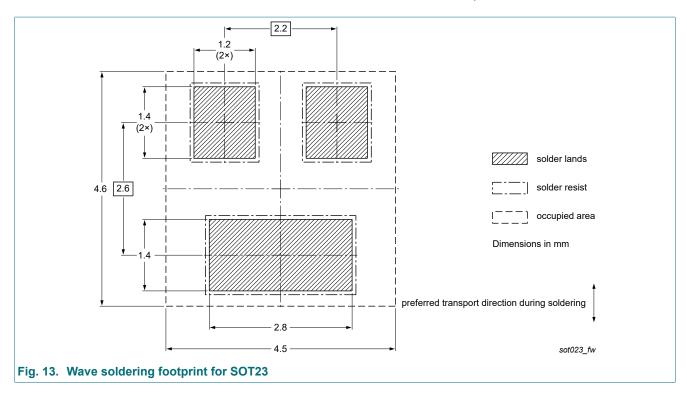
11. Package outline



12. Soldering



50 V; 3 A NPN low VCEsat transistor



50 V; 3 A NPN low VCEsat transistor

13. Revision history

Table 8. Revision history

Table 0. Nevision history								
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes				
PBSS4350T v.4	20230101	Product data sheet	-	PBSS4350T v.3				
Modifications:		 Product changed to non-automotive qualification. Please refer to nexperia.com for automotive(-Q) product alternative(s). 						
PBSS4350T v.3	20220510	Product data sheet	-	PBSS4350T v.2				
PBSS4350T v.2	20040109	Product data sheet	-	PBSS4350T v.1				
PBSS4350T v.1	20020808	Product data sheet	-	-				

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14. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- 2] The term 'short data sheet' is explained in section "Definitions".
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50 V; 3 A NPN low VCEsat transistor

Contents

1.	General description	1
2.	Features and benefits	1
3.	Applications	1
4.	Quick reference data	1
5.	Pinning information	2
6.	Ordering information	2
7.	Marking	2
8.	Limiting values	3
9.	Thermal characteristics	4
10.	Characteristics	5
11.	Package outline	9
12.	Soldering	9
13.	Revision history	11
14.	Legal information	12

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